

## CURRICULUM VITAE

Konstantinos D. Kourkoutas

### Personal data

Place of birth: Athens

Date of birth: April 9, 1951

Family status: married to Flora P. Papapolychroniou since 1992

Occupation: Professor in the Department of Physics Chemistry and Material Technology of the Technical Educational Institute of Athens (1986- )

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### Academic degrees

Physics Diploma (1975, University of Athens)

Master in Electronic Automation (1982, University of Athens)

Doctorate in Physics (1984, University of Athens)

### Scientific interests

Conductivity, magnetic and optical properties of semiconductors and semiconductor devices.

Luminescence emission properties of crystal scintillators under X-ray exposure.

## Other interests

Numerical Analysis and Number Theory

## Publications and contribution to recent Conferences

1. C. D. Kourkoutas, P. D. Bekris, G. J. Papaioannou and P. C. Euthymiou: Transport Parameters of n-type GaSb, Solid State Communications 49, 1071, (1984)
2. C. D. Kourkoutas, P. D. Bekris, G. J. Papaioannou and P. C. Euthymiou: Anomalous Magnetoresistance Effects in Te doped GaSb, Solid State Communications, 55, 881, (1985)
3. P. C. Euthymiou, G. J. Papaioannou, J. A. Kaliakatsos, C. D. Kourkoutas and P. C. Banbury: Electron Damage Studies in GaP at low Temperatures, Solid State Communications, 58, 193, (1986)
4. P. C. Euthymiou, G. J. Papaioannou, C. D. Kourkoutas and P. C. Banbury: Transport Parameters in illuminated Layers of semiinsulating GaAs, Solid State Communications, 62, 423, (1987)
5. G. J. Papaioannou, C. D. Kourkoutas, N. G. Theofanous and T. A. Arapoyanni: A study of the Gain Mechanisms in GaAs Planar Photoconductive Detectors, Physica Status Solidi (a) 104, K141, (1987)
6. C. D. Kourkoutas, G. J. Papaioannou, P. C. Euthymiou and G. E. Zardas: Determination of the scattering Mechanisms in p-type Semiconductors of the III-V Group. The case of Zn doped GaP and natural (undoped) GaSb, Solid State Communications, 67, 651, (1988)
7. G. J. Papaioannou, E. Anagnostakis, P. C. Euthymiou, C. D. Kourkoutas and G. E. Zardas: On the impurity photoconductivity of semiinsulating GaP:Cr, Physica Status Solidi (a) 114, K215, (1989)
8. P. C. Banbury, P. C. Euthymiou, C. D. Kourkoutas and G. E. Zardas: DLTS Studies of Defects in GaP:Te before and after Irradiation, Solid State Communications, 74, 305, (1990)
9. C. D. Kourkoutas, P. C. Euthymiou and G. J. Papaioannou: Dependence of the Mobility Limit upon the Fermi Level Position in direct Gap III-V Group Semiconductors, Solid State Communications, 74, 999, (1990)
10. G. E. Zardas, P. C. Euthymiou, B. Szentpali, Ch. Symeonidis and K. Kourkoutas: Dependence of I-V Characteristics of GaAs MESFETs on Temperature and alpha Particle Irradiation, Physica Status Solidi (a), 123, K79, (1991)

11. C. D. Kourkoutas, J. Novak, M. Kulifayova, G. J. Papaioannou, P. Kordos and V. Ioannou- Sougleridis: Transport properties of Praseodymium doped p-type  $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$  Layers, *Solid State Communications*, 78, 543, (1991)
12. C. D. Kourkoutas, P. C. Euthymiou, B. Szentpali, B. Kovacs and K. Somogyi: Correction of the Drift Mobility Measurements in GaAs MESFETs, *Solid State Communications*, 78, 849, (1991)
13. B. Szentpali, B. Kovacs, D. Huber, C. D. Kourkoutas, P. C. Euthymiou and G. E. Zardas: Effect of Electron Irradiation on the Mobility Profile in GaAs FATFETs, *Solid State Communications*, 80, 321, (1991)
14. Kourkoutas: The PHOTOFET Method in submicron GaAs MESFETs: Substrate leakage current effect, *Semiconductors Science and Technology*, 7, 935, (1992)
15. G. E. Zardas, P. C. Euthymiou, Ch. Symeonidis, C. D. Kourkoutas and P. H. Yannakopoulos: Effect of alpha Particles Irradiation on AlGaAs/GaAs Planar Photoconductive Detectors at low Temperatures, *Physica Status Solidi (a)*, 133, K49, (1992)
16. C. D. Kourkoutas, B. Kovacs, P. C. Euthymiou, B. Szentpali, K. Somogyi, P. C. Banbury and G. E. Zardas: The Effect of Electron Irradiation Dose on the Profile of electric G. J. Papaioannou, V. Ioannou-Sougleridis, T. Lalinski, J. Kuzmik, M. Porges and C. D. Characteristics in GaAs VPE Layers: *Physica Status Solidi (a)*, 135, K21 (1993)
17. Yu. A. Aleschenko, E. A. Bobrova, V. S. Vavilov, L. K. Vodopyanov, G. N. Galkin, M. V. Chukichev, R. R. Resvanov, P. Euthymiou, C. Kourkoutas, P. Bekris, S. U. Sokolov, T. A. Kuzemchenko, D. L. Khavroshin: Long Range Effect in Ion Implanted GaAs, *Radiation Effects and Defects in Solids*, 25, 323, (1993)
18. P. C. Euthymiou, G. E. Zardas, Ch. Symeonidis, P. C. Banbury and C. D. Kourkoutas: Effect of  $\alpha$ -Particle Irradiation on GaAs Planar Photoconductive Detectors at low Temperatures, *Physica Status Solidi (a)*, 139, K113, (1993)
19. C. D. Kourkoutas, B. Kovacs, P. C. Euthymiou, B. Szentpali, K. Somogyi and G. E. Giakoumakis: A study of the profile of the E3 Electron Trap in GaAs, *Solid State Communications*, 89, (1), 45, (1994)
20. C. D. Kourkoutas and G. J. Papaioannou: A fast Solution of Poissons Equation in FETs, *Solid State Electronics*, 37, (2), 373, (1994)
21. P. C. Euthymiou, C. D. Kourkoutas, B. Szentpali, B. Kovacs, K. Somogyi, P. C. Banbury, G. E. Zardas and G. E. Giakoumakis: A Review Article on the Transport Properties in FATFETs upon Irradiation, *Acta Physica Hungarica* 74 (1-2), 7, (1994)
22. Investigation of the effect of the scintillator material on the overall X-ray detection system performance by application of analytical models. N. Eftimiou, N. Kalivas, G. Patatoukas, A. Konstantinidis, I. Valais, D. Nikolopoulos, A. Gaitanis, S. David, C. Michail, G. Loudos, D. Cavouras, K. Kourkoutas, G. Panayiotakis and I. Kandarakis. *Euromedim 2006: 1st*

European Conference on Molecular Imaging Technology, Marseille, France, 9-12 May 2006

23. Investigation of luminescence emission properties of  $(\text{Lu},\text{Y})_2\text{SiO}_5:\text{Ce}$  (LYSO:Ce) and  $(\text{Lu},\text{Y})\text{AlO}_3:\text{Ce}$  (LuYAP:Ce) single crystal scintillators under x-ray exposure for use in medical imaging. Ioannis G. Valais, Stratos L. David, Christos M. Michail, Dimitrios N. Nikolopoulos, Dionisis A. Cavouras, Ioannis, A. Sianoudis, Constantinos D. Kourkoutas, Ioannis S. Kandarakis and George S. Panayiotakis. IEEE, Nuclear Science Symposium, Medical Imaging Conference, San Diego, California, on Oct. 29 - Nov. 4, 2006.